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concl'd. patent no. 5,976,940. Moreover, this patent claims priority to Japanese Application No. P07-322962, filed December 12, 1995, which application is incorporated by reference to the extent permitted by law.--.

5 On page 21, line 12, replace "first embedded diffusion layer 131 has" with --first embedded diffusion layer 131 may include a peak position 600 of an impurity concentration that may reside at a first distance from a datum surface of the substrate 111 (for example an arbitrary surface used as a  
10 reference, such as a bottom surface of the substrate 111). The first embedded diffusion layer 131 has--.

G2 On page 22, line 2, replace "high." with --high. Additionally, the second embedded diffusion layer 151 may include a peak position 700 of an impurity concentration that  
15 may reside at a second distance from the datum surface of the substrate 111 such that the first distance (peak position 600 of Figure 6 to the datum surface of the substrate 111) may be greater than the second distance (peak position 700 of Figure 7 to the datum surface of the substrate 111).--

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IN THE CLAIMS

Please amend claims 1, 3, 4, 6, 17, 19 and 20 and add new  
Sub H claims 21-23 as follows:

G3 1. (Amended Five Times) A semiconductor device,  
2 comprising:  
3 [a first vertical type bipolar transistor and a second  
4 vertical type bipolar transistor whose voltage is different  
5 from that of said first vertical type bipolar transistor  
6 formed on a semiconductor substrate made by forming]  
7 a substrate defining a datum surface;